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Electron dynamics in magnetron sputtering discharges

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Outline

- Particle-In-Cell/Monte Carlo Collision (PIC/MCC)
- Radio Frequency Magnetron Sputtering (RFMS)
- Direct Current Magnetron Sputtering (DCMS)
- Pulsed DCMS
- High Power Impulse Magnetron Sputtering (HiPIMS)



PIC/MCC simulation

- Advantages
 - Self-consistent
 - Complete
- ASTRA
 - Efficient PIC software
 - Applications in
 - Ion sources
 - Microplasmas
 - RF plasmas
 - Magnetized plasmas
 - etc.

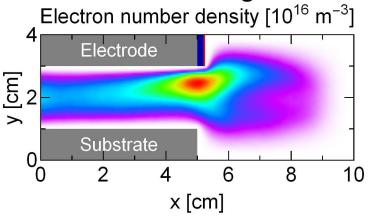


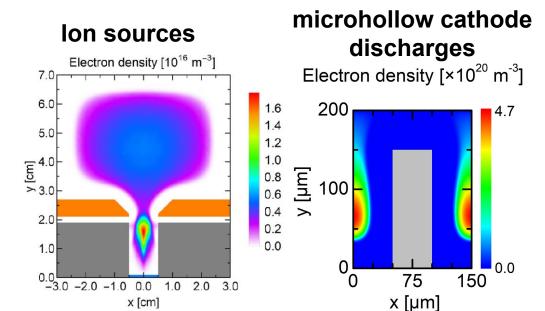
0.8

0.6

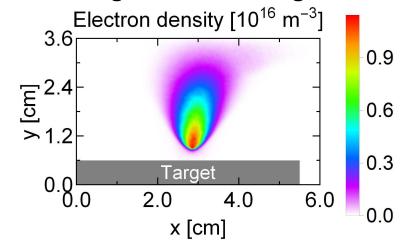
0.4

0.2



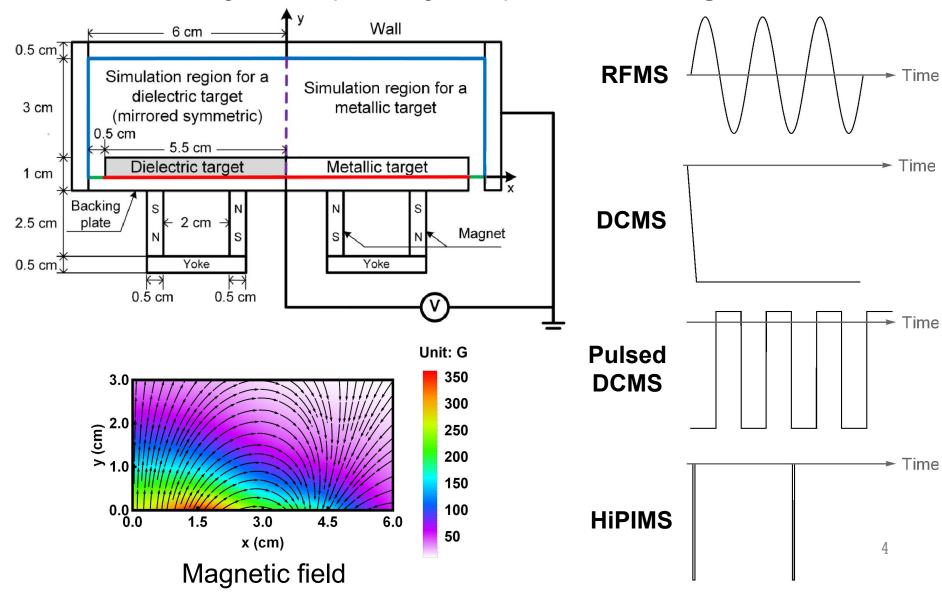






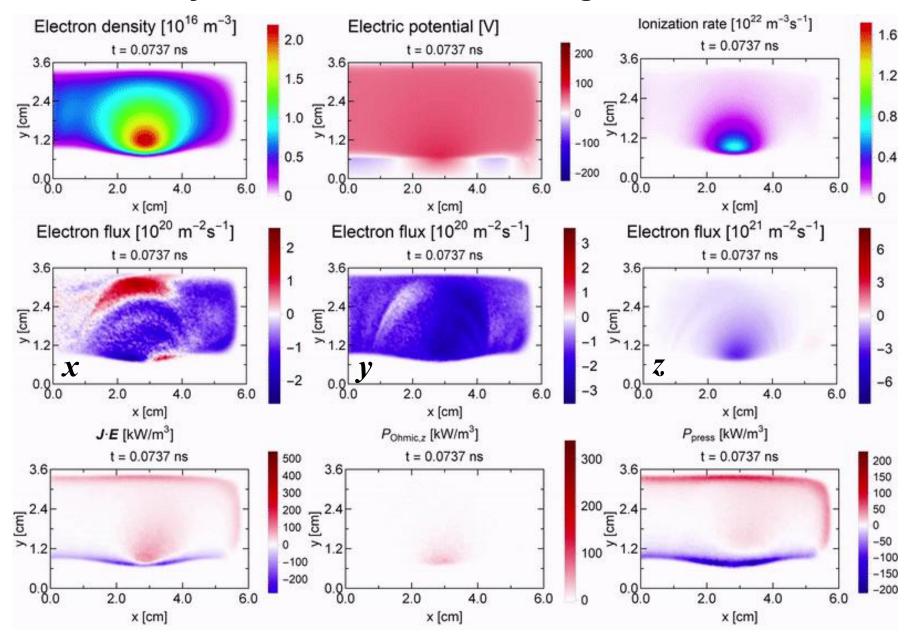
Magnetron sputtering discharges

Schematic of a magnetron sputtering set-up

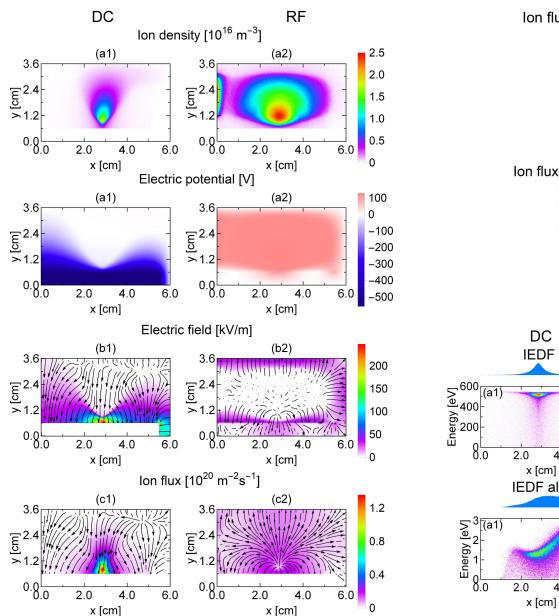


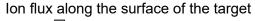
Voltage waveforms

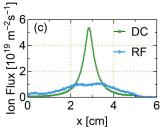
Electron dynamics in RFMS discharges



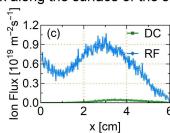
RFMS vs DCMS



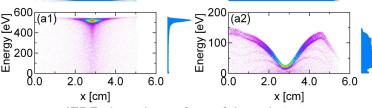




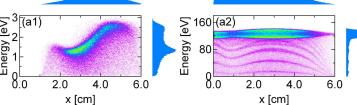
Ion flux along the surface of the substrate



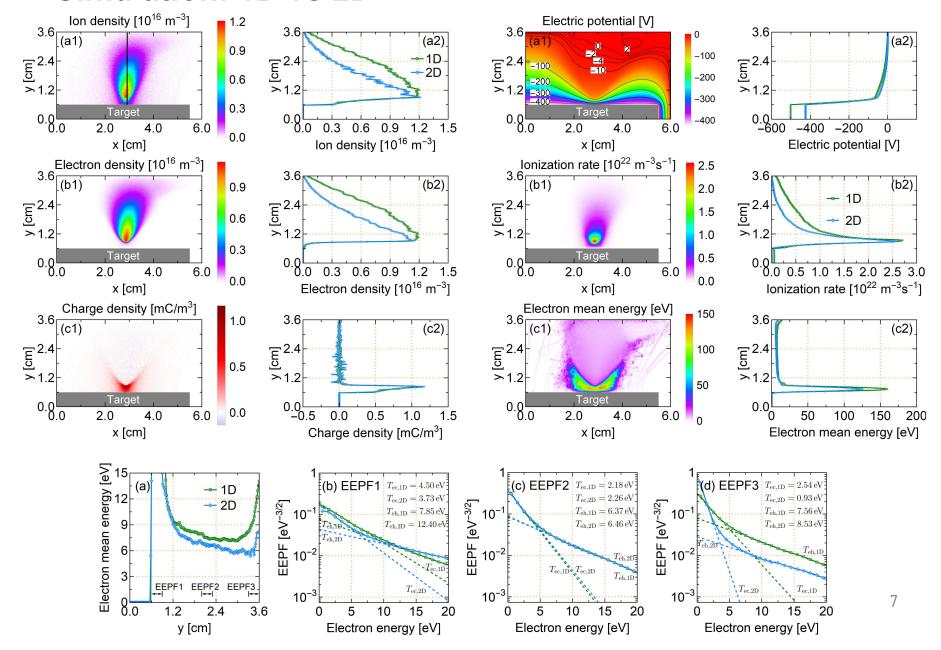
DC RF IEDF along the surface of the target



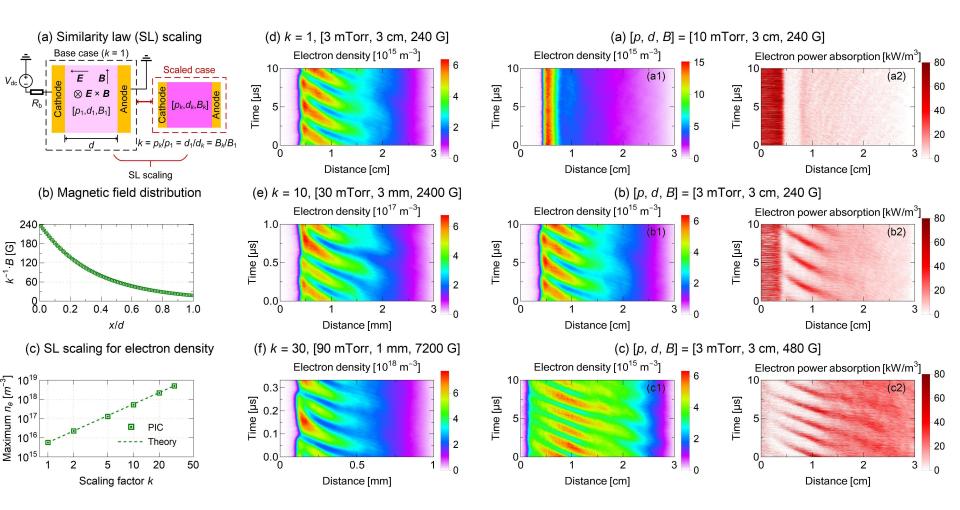
IEDF along the surface of the substrate



Simulation: 1D vs 2D



DCMS: breathing oscillations and electron energization







Pulsed DCMS $T_{on}/T_{off} = 1/1$ $T_{on}/T_{off} = 1/1$ $T_{\rm on}/T_{\rm off} = 1/1$ — 4/1 --9/1Electron density [10¹⁶ m⁻³] Ionization rate [10²¹ m⁻³s⁻¹] 10 0.8 10₁ Voltage [V] Time [µs] Time [µs] 0.6 6 -200 0.4 -400 0.2 2 10 2 8 0 3 0.0 Distance [cm] Time [µs] Distance [cm] $T_{on}/T_{off} = 4/1$ $T_{on}/T_{off} = 4/1$ Electron density [10¹⁶ m⁻³] Ionization rate [10²¹ m⁻³s⁻¹] 0.5 10₁ 0.8 10₁ Current [mA] Time [µs] Time [µs] 0.6 0.0 6 0.4 -0.5 0.2 2 2 3 2 0.0 10 6 Distance [cm] Distance [cm] Time [µs] $T_{on}/T_{off} = 9/1$ $T_{on}/T_{off} = 9/1$ Electron density [10¹⁶ m⁻³] Ionization rate [10²¹ m⁻³s⁻¹] 0.3 10₁ 0.8 10 Power [W] 0.2 Time [µs] Time [µs] 0.6 6 5 0.1 0.4 0.0 0.2 -0.1

Distance [cm]

2

Time [µs]

8

10

3

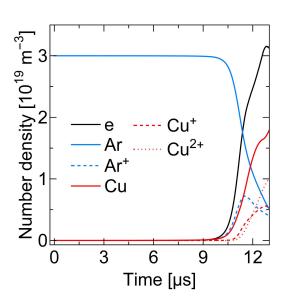
0.0

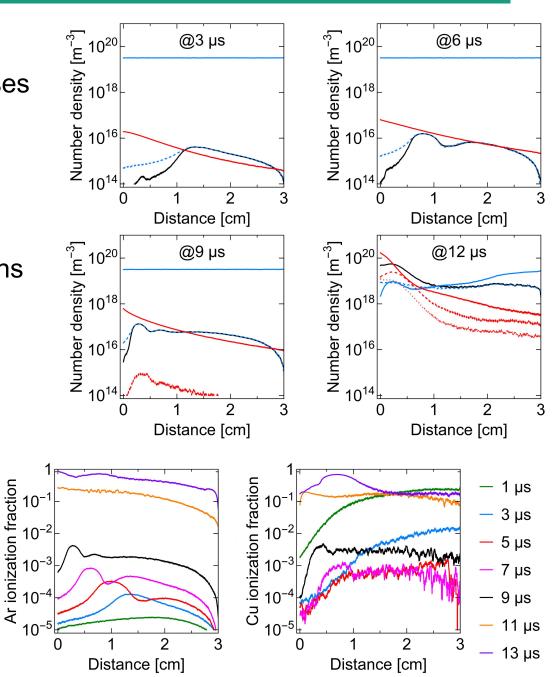
2

Distance [cm]

HiPIMS

- Additional physical processes
 - Coulomb collisions
 - Sputtering wind
 - Metal ions
 - SEE induced by metal ions







Thank you

- ■The slides can be downloaded at bczheng.com/talks/zheng21_icmap.pdf
- Email: bzheng@fraunhofer.org
- ■Website: <u>bczheng.com</u>